

### INCHANGE SEMICONDUCTOR

## **isc** Silicon NPN Darlington Power Transistor

# 2SD2093

### DESCRIPTION

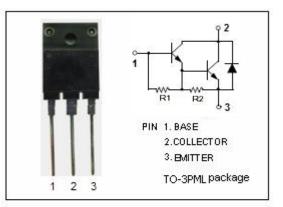
- Micaless package facilitating mounting.
- Large current capacity and large ASO.
- · Low saturation volatage.
  - : V<sub>CE(sat)</sub>= 1.5V(Max) @I<sub>C</sub>= 5A,I<sub>B</sub>=10mA
- High DC Current Gain
  - : h<sub>FE</sub>= 1500(Min) @ I<sub>C</sub>= 5A, V<sub>CE</sub>= 3V
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

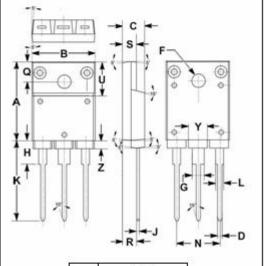
#### **APPLICATIONS**

• Designed for Motor drivers, printer hammer drivers relay drivers, voltage regulator control applications

### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>сво</sub>	Collector-Base Voltage	110	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	100	V	
V <sub>EBO</sub>	Emitter-Base Voltage	6	V	
lc	Collector Current-Continuous	10	А	
I <sub>CM</sub>	Collector Current-Peak	15	А	
Pc	Collector Power Dissipation @ $T_c=25^{\circ}C$	45	14/	
	Collector Power Dissipation @ T <sub>a</sub> =25°C	3	W	
TJ	Junction Temperature	150	°C	
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C	





	mm	
DIM	MIN	MAX
A	19.90	20.10
В	15.75	16.10
С	5.50	5.70
D	0.90	1.10
F	3.30	3.50
G	2.90	3.20
Н	5.90	6.10
J	0.595	0.70
K	21.10	22.50
L	1.90	2.25
N	10.80	11.00
0	4.90	5.10
R	3.75	3.95
S	3.20	3.60
U	9.90	10.10
Y	4.20	4.90
Z	1.90	2.10

isc website: www.iscsemi.com



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### **ELECTRICAL CHARACTERISTICS**

#### $T_{c}\text{=}25^{\circ}\!\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	$I_{C}$ = 10mA ; $R_{BE}$ = $\infty$	100			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>E</sub> = 0	110			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> =5A; I <sub>B</sub> = 10mA			1.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 10mA			2.0	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 80V; I <sub>E</sub> = 0			100	μA
I <sub>EbO</sub>	Collector Cutoff Current	V <sub>Eb</sub> = 5V; R <sub>BE</sub> = ∞			3	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 5A; V <sub>CE</sub> = 3V	1500			

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